

EAST - [10666JJG.wsp:1] [x]

File View Edit Tools Window Help

L13: (386) 12 and (contact)  
 L14: (3) 12 and (contact adj pillar)  
 L15: (383) (13 not 14) and (method or process)  
 L16: (383) 15 and (method or process)  
 L17: (131) 16 and (second adj (dielectric or insula  
 L18: (82) 17 and ((second adj (dielectric or insula  
 L19: (69) 18 and (capacitor with (plate or electrod  
 L20: (66) 19 and expos\$4  
 L21: (60) 20 and (expos\$4 with (etch\$4 or remov\$4))  
 L22: (5) 21 and (ground adj (plate or electrode))  
 L23: (0) 20040012022.URPN.  
 L24: (1) "6562679".PN.  
 L25: (0) 6727542.URPN.  
 L26: (9) ("4864374" | "5229326" | "5998225" | "6236  
 L27: (0) 6746915.URPN.  
 L28: (0) 6746915.URPN.  
 L29: (55) 21 not 22  
 L30: (3) memory and capacitor and (contact adj pill  
 L31: (10) ("4994893" | "5045899" | "5475248" | "562  
 L32: (0) 6710201.URPN.

**Browsing** **Search** **Browser** **Queue** **Clear**  
**DBs:** USPAT, US-PGPUB, EPO, JPQ, IBM-TDB  Plurals  Highlight all hit terms initially  
**Default operator:** OR

21 and (ground adj (plate or electrode))

File Edit View Insert Tools Options Help

**Document ID** **Issue Date** **Pages** **Title** **Current OR** **Current XI**

1	<input type="checkbox"/> <input checked="" type="checkbox"/> <input type="checkbox"/> <input type="checkbox"/> US 20040012022	20	Stack-type DRAM memory structure and its manufacturing method	257/68	257/300; 257/71;
2	<input type="checkbox"/> <input checked="" type="checkbox"/> <input type="checkbox"/> <input type="checkbox"/> US 20030132429	21	Semiconductor memory device and method for manufacturing the same	257/1	257/43; 257/E21.01
3	<input type="checkbox"/> <input checked="" type="checkbox"/> <input type="checkbox"/> <input type="checkbox"/> B2 US 6746915 20040608	19	Stack-type DRAM memory structure and its manufacturing method	438/253	257/300; 257/296;
4	<input type="checkbox"/> <input checked="" type="checkbox"/> <input type="checkbox"/> <input type="checkbox"/> B2 US 6727542 20040427	18	Semiconductor memory device and method for manufacturing the same	257/306	257/303; 257/309
5	<input type="checkbox"/> <input checked="" type="checkbox"/> <input type="checkbox"/> A US 5665624 19970909	9	Method for fabricating trench/stacked capacitors on DRAM cells with increased capacitance	438/244	257/E27.09

File Edit View Insert Tools Options Help

Ready NUM